

ABSTRACT

WAFER PRODUCING METHOD

A wafer producing method for producing a hexagonal single crystal wafer from a hexagonal single crystal ingot is disclosed. The wafer producing method includes a separation start point forming step of forming a modified layer parallel to the upper surface of the ingot and cracks extending from the modified layer to thereby form a separation start point in the ingot. The separation start point forming step includes a first separation start point forming step of setting the focal point of a laser beam at a first depth which is N times (N is an integer not less than 2) the depth corresponding to the thickness of the wafer from the upper surface of the ingot and next applying the laser beam to the ingot to thereby form a first separation start point composed of a first modified layer and first cracks extending therefrom.

(Figure 11C)